

1. Record Nr.	UNISA990002413320203316
Autore	PIANEZZOLA, Emilio
Titolo	Dieci secoli di letteratura latina : antologia di testi e traduzioni / Emilio Pianezzola, Lucio Cristante, Giovanni Ravenna
Pubbl/distr/stampa	Firenze : Le Monnier, 1995
ISBN	88-00-42003-6
Edizione	[Nuova ed. rinnovata e aumentata]
Descrizione fisica	IV, 997 p. ; 24 cm
Altri autori (Persone)	CRISTANTE, Lucio RAVENNA, Giovanni
Disciplina	870.8001
Soggetti	Letteratura latina - Antologie
Collocazione	V.3.C. 61(VIII C 1470)
Lingua di pubblicazione	Italiano
Formato	Materiale a stampa
Livello bibliografico	Monografia

2. Record Nr.	UNINA9910841712403321
Autore	Bernstein Joseph B
Titolo	Reliability Prediction for Microelectronics
Pubbl/distr/stampa	Newark : , : John Wiley & Sons, Incorporated, , 2024 ©2024
ISBN	1-394-21096-5 1-394-21094-9
Edizione	[1st ed.]
Descrizione fisica	1 online resource (401 pages)
Collana	Quality and Reliability Engineering Series
Altri autori (Persone)	BensoussanAlain BenderEmmanuel
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Nota di contenuto	Cover -- Title Page -- Copyright Page -- Dedication Page -- Contents -- Author Biography -- Series Foreword -- Preface -- Scope -- Introduction -- Chapter 1 Conventional Electronic System Reliability Prediction -- 1.1 Electronic Reliability Prediction Methods -- 1.2 Electronic Reliability in Manufacturing, Production, and Operations -- 1.2.1 Failure Foundation -- 1.2.2 Reliability Foundational Models (Markovian, Gamma, Lévy, Wiener Processes) -- 1.2.3 Correlation Versus Causation and Representativeness of Trackers -- 1.2.4 Functional Safety Standard ISO 26262 -- 1.2.5 Additional Considerations -- 1.3 Reliability Criteria -- 1.3.1 The Failure Rate Curve for Electronic Systems -- 1.3.2 Basic Lifetime Distribution Models -- 1.4 Reliability Testing -- 1.4.1 Reliability Test Methods -- 1.4.2 Accelerated Testing -- Chapter 2 The Fundamentals of Failure -- 2.1 The Random Walk -- 2.1.1 Approximate Solution -- 2.1.2 Constant Velocity -- 2.2 Diffusion -- 2.2.1 Particle Diffusion -- 2.3 Solutions for the Diffusion Equation -- 2.3.1 Normal Distribution -- 2.3.2 Error Function Solution -- 2.3.3 Finite Thickness -- 2.3.4 Thermal Diffusion -- 2.4 Drift -- 2.5 Statistical Mechanics -- 2.5.1 Energy -- 2.6 Chemical Potential -- 2.6.1 Thermodynamics -- 2.7 Thermal Activation Energy -- 2.7.1 Arrhenius Relation -- 2.7.2 Einstein Relation -- 2.7.3 Magnitude of Energy -- 2.8 Oxidation and Corrosion -- 2.8.1 Reaction

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